

ABSTRACT

A compound semiconductor light-emitting diode comprising
a light-emitting layer composed of a Group III-V compound
5 semiconductor, and a current diffusion layer provided on the
light-emitting layer and composed of a Group III-V compound
semiconductor, characterized in that the current diffusion
layer is composed of a conductive boron-phosphide-based
semiconductor and has a bandgap at room temperature wider
10 than that of the light-emitting layer.